IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of:	**Koji SAKUI et al.**	Atty. Docket No.:	001701.00236
Serial No.:	10/638,406	Group Art Unit:	2818
Filed:	August 12, 2003	Examiner:	Unknown
For:	NONVOLATILE SEMICONDUCTOR MEMORY	Confirmation No.:	5160

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT UNDER 37 C.F.R. § 1.97(b)

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

In accordance with Applicants' duty of disclosure, the following information is submitted for consideration by the United States Patent and Trademark Office in connection with the above-captioned application. The information is identified on the attached PTO 1449 form.

In accordance with the waiver of the requirement under 37 C.F.R. § 1.98(a)(2)(i) set forth in the OG Notice dated August 5, 2003, Applicants are providing copies of foreign patent and non-patent literature documents only.

The undersigned certifies under 37 C.F.R. § 1.97(e)(1) that each reference cited herein was cited in a communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this statement.

Also enclosed is a copy of the search report for a corresponding foreign application indicating the relevance of the references cited therein.

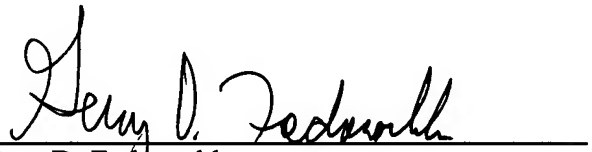
Applicants do not waive any right to take appropriate action to establish patentability over the listed documents should they be applied as references against the claims of the present application.

It is respectfully requested that the Examiner fully consider each of the documents, initial the enclosed Form PTO-1449 in the appropriate place to indicate that the document has been considered, and return a copy of the initialed form to the undersigned in accordance with MPEP Section 609.

Applicants believe that no fee is necessary pursuant to 37 C.F.R. § 1.97(b). However, if a fee is due, the Office is authorized to charge Deposit Account No. 19-0733.

Respectfully submitted,

BANNER & WITCOFF, LTD.

Dated: March 16, 2004 By: 

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Substitute for form 1449A/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

Sheet 1 of 1

Complete if Known	
Application Number	10/638,406
Filing Date	August 12, 2003
First Named Inventor	Koji Sakui et al.
Group Art Unit	2818
Examiner Name	Unknown
Attorney Docket Number	01701.00236

U.S. PATENT DOCUMENTS

Examiner Initials *	Cite No.[1]	U.S. Patent Document Number	U.S. Patent Document Kind Code[2] (*if known*)	Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		5515327		Matsukawa et al.	5-7-1996	
		5559735		Ono et al.	9-24-1996	
		5523980		Sakui et al.	6-4-1996	
		5615163		Sakui et al.	3-25-1997	
		4996669		Endoh et al.	2-26-1991	

FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No.[1]	Foreign Patent Document Office[3]	Number[4]	Kind Code[5] (*if known*)	Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T[6]
		EP	0797212	A2	Toshiba	9-24-1997		x
		JP	10-177797	A	Toshiba	6-30-1998		abst

OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials *	Cite No.[1]	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T[2]
		Takeuchi, Ken, et al., "A Double-Level-V_{th} Select Gate Array Architecture for Multilevel NAND Flash Memories," IEICE Trans. Electron., Vol. E79-C, No. 7, July 1, 1996, pp. 1013-1020	
		Choi, J.D., et al., "A New Double Boosting Program Scheme in Booster Plate NAND Flash Memories with 9V Programming," Non-Volatile Semiconductor Memory Workshop, August 1998, pp. 109-111	

Examiner Signature		Date Considered	

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.